

# RJK6009DPP

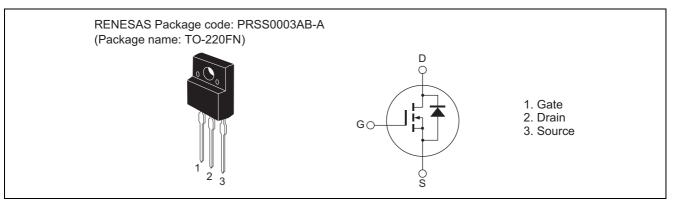
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1607-0100 Rev.1.00 Dec 04, 2007

## Features

- Low on-resistance
- Low leakage current
- High speed switching

## Outline



## **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	(1a – 23 C) Unit
Drain to source voltage	V <sub>DSS</sub>	600	V
Gate to source voltage	V <sub>GSS</sub>	±30	V
Drain current	I <sub>D</sub> <sup>Note4</sup>	18	А
Drain peak current	I <sub>D (pulse)</sub> Note1	54	А
Body-drain diode reverse drain current	I <sub>DR</sub>	18	А
Body-drain diode reverse drain peak current	I <sub>DR (pulse)</sub> Note1	54	А
Avalanche current	I <sub>AP</sub> <sup>Note3</sup>	4	А
Avalanche energy	E <sub>AR</sub> <sup>Note3</sup>	0.87	mJ
Channel dissipation	Pch Note2	40	W
Channel to case thermal impedance	θch-c	3.125	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

2. Value at Tc =  $25^{\circ}C$ 

3. STch =  $25^{\circ}$ C, Tch  $\leq 150^{\circ}$ C

4. Limited by maximum safe operation area

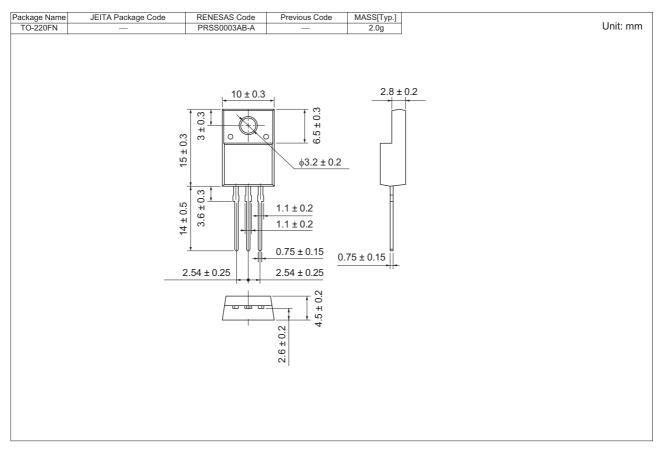
## **Electrical Characteristics**

 $(Ta = 25^{\circ}C)$ 

ltem	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	600			V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	—	1	μΑ	$V_{DS} = 600 \text{ V}, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>		_	±0.1	μΑ	$V_{GS}=\pm 30~V,~V_{DS}=0$
Gate to source cutoff voltage	V <sub>GS(off)</sub>	3.0	_	4.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state	R <sub>DS(on)</sub>	_	0.392	0.480	Ω	$I_D = 9 \text{ A}, V_{GS} = 10 \text{ V}^{Note5}$
resistance						
Input capacitance	Ciss	_	2100		pF	V <sub>DS</sub> = 25 V
Output capacitance	Coss	_	205	_	рF	V <sub>GS</sub> = 0 f = 1 MHz
Reverse transfer capacitance	Crss	_	25	_	рF	
Turn-on delay time	t <sub>d(on)</sub>		35	_	ns	I <sub>D</sub> = 9 A
Rise time	tr	_	28		ns	
Turn-off delay time	t <sub>d(off)</sub>		99	_	ns	
Fall time	t <sub>f</sub>		18	_	ns	
Total gate charge	Qg	-	54	_	nC	$V_{DD} = 480 V$ $V_{GS} = 10 V$ $I_D = 18 A$
Gate to source charge	Qgs		10		nC	
Gate to drain charge	Qgd		22	_	nC	
Body-drain diode forward voltage	V <sub>DF</sub>	_	0.9	1.5	V	$I_F = 18 \text{ A}, V_{GS} = 0^{\text{Note5}}$
Body-drain diode reverse recovery time	t <sub>rr</sub>	_	390	—	ns	$I_F = 18 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu s$

Notes: 5. Pulse test

## **Package Dimensions**



## **Ordering Information**

Part Name	Quantity	Shipping Container
RJK6009DPP-00-T2	1050 pcs	Box (Tube)

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